

### DESCRIPTION

The MP9485 is a high-voltage, step-down, switching regulator that delivers up to 0.5A of current to the load. It integrates a high-side, high-voltage power MOSFET with a current limit of 1.0A, typically. The wide 4.5V to 100V input range accommodates a variety of step-down applications, making it ideal for automotive, industry, and lighting applications. Hysteretic voltage-mode control is employed for very fast response. MPS's proprietary feedback control scheme minimizes the number of required external components.

The switching frequency can be up to 2MHz, allowing for small component size. Thermal shutdown and short-circuit protection (SCP) provide reliable and fault-tolerant operations. A 170µA quiescent current allows the MP9485 to be used in battery-powered applications.

The MP9485 is available in a SOIC-8 package with an exposed pad.

### FEATURES

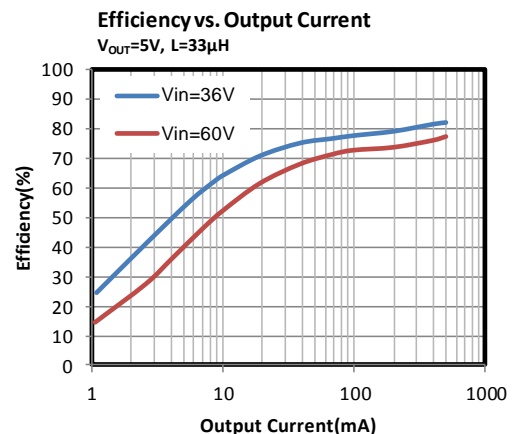
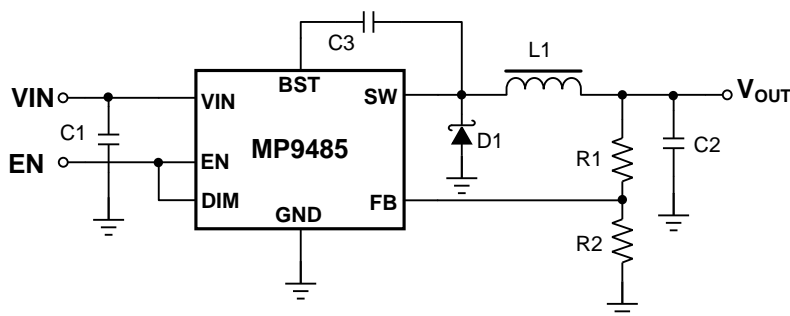
- Wide 4.5V to 100V Input Range
- Hysteretic Control: No Compensation
- Up to 2MHz Switching Frequency
- PWM Dimming Control Input for LED Application
- Short-Circuit Protection (SCP) with Integrated High-Side MOSFET
- 170µA Quiescent Current
- Thermal Shutdown
- Available in a SOIC-8 Package with an Exposed Pad

### APPLICATIONS

- E-Bike Control Power Supplies
- Solar Energy Systems
- Automotive System Power
- Industrial Power Supplies
- High-Power LED Drivers

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### TYPICAL APPLICATION



## ORDERING INFORMATION

Part Number*	Package	Top Marking
MP9485GN	SOIC-8 EP	See Below

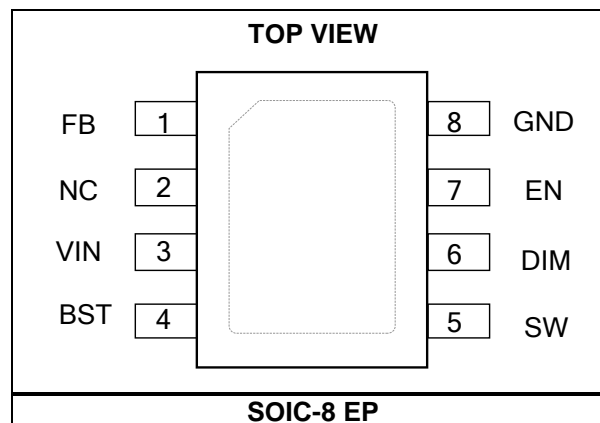
\* For Tape & Reel, add suffix -Z (e.g. MP9485GN-Z)

## TOP MARKING

**MP9485**  
**LLLLLLLL**  
**MPSYWW**

MP9485: Product code of MP9485GN  
 LLLLLLLL: Lot number  
 MPS: MPS prefix  
 Y: Year code  
 WW: Week code

## PACKAGE REFERENCE



# ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

Supply voltage (V <sub>IN</sub> ).....	-0.3V to +100V
Switch voltage (V <sub>SW</sub> )...-0.5V (-4V for <10ns)	to V <sub>IN</sub> + 0.5V
BST to SW .....	-0.3V to +6V
All other pins.....	-0.3V to +6V
Junction temperature .....	150°C
Continuous power dissipation (T <sub>A</sub> = +25°C) <sup>(2)</sup>	2.5W
Lead temperature .....	260°C
Storage temperature.....	-65°C to +150°C

# Recommended Operating Conditions <sup>(3)</sup>

Supply voltage (V <sub>IN</sub> ).....	4.5V to 95V
EN and DIM voltages.....	0V to 5V
Max switching frequency .....	2MHz
Operating junction temp.....	-40°C to +125°C

Thermal Resistance <sup>(4)</sup>	$\theta_{JA}$	$\theta_{JC}$
SOIC-8 EP .....	50.....	10.. °C/W

# NOTES:

- 1) Exceeding these ratings may damage the device.
- 2) The maximum allowable power dissipation is a function of the maximum junction temperature T<sub>J</sub>(MAX), the junction-to-ambient thermal resistance  $\theta_{JA}$ , and the ambient temperature T<sub>A</sub>. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P<sub>D</sub>(MAX)=(T<sub>J</sub>(MAX)-T<sub>A</sub>)/ $\theta_{JA}$ . Exceeding the maximum allowable power dissipation produces an excessive die temperature, causing the regulator to go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
- 3) The device is not guaranteed to function outside of its operating conditions.
- 4) Measured on JESD51-7 4-layer board.

## ELECTRICAL CHARACTERISTICS

$V_{IN} = 60V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted. Specifications over temperature are guaranteed by design and characterization.

Parameter	Symbol	Condition	Min	Typ	Max	Units
VIN UVLO threshold			3.6	4.0	4.4	V
VIN UVLO hysteresis				0.4		V
Shutdown supply current		$V_{EN} = 0V$		2	5	$\mu A$
Quiescent supply current		No load, $V_{FB} = 250mV$		170	220	$\mu A$
Upper switch on resistance <sup>(5)</sup>	$R_{DS(ON)}$	$V_{BST} - V_{SW} = 5V$		500		$m\Omega$
Upper switch leakage current	$I_{SWLK}$	$V_{EN} = 0V$ , $V_{SW} = 0V$		0.01	1	$\mu A$
Current limit	$I_{PK}$	$V_{FB} = 0.15V$	0.75			A
EN up threshold	$V_{ENH}$		1.4	1.55	1.7	V
EN threshold hysteresis	$V_{ENHY}$			320		mV
EN input current	$I_{ENI}$	$V_{EN} = 5V$		0.01	1	$\mu A$
EN sinking current	$I_{ENS}$	$V_{EN} = 2V$		2	3	$\mu A$
DIM up threshold	$V_{DIMH}$		0.8	1.15	1.5	V
DIM threshold hysteresis	$V_{DIMHY}$			300		mV
DIM input current	$I_{DIM}$	$V_{DIM} = 5V$ or $0V$	-1		1	$\mu A$
DIM on propagation delay	$T_{DIMDH}$	$V_{FB} = 0V$ , $V_{DIM}$ rising edge to $V_{SW}$ rising edge		50		ns
DIM off propagation delay	$T_{DIMDL}$	$V_{FB} = 0V$ , $V_{DIM}$ falling edge to $V_{SW}$ falling edge		50		ns
FB voltage threshold high <sup>(5)</sup>	$V_{FBH}$	$4.5V < V_{IN} < 95V$ , $V_{FB}$ rising from $0V$ until $V_{SW} < 30V$	209	215	221	mV
FB voltage threshold low <sup>(5)</sup>	$V_{FBL}$	$4.5V < V_{IN} < 95V$ , $V_{FB}$ falling from $0.25V$ until $V_{SW} > 30V$	179	185	191	mV
FB input current	$I_{FB}$	$V_{FB} = 5V$ or $0V$	-300		300	nA
FB propagation delay to output high	$T_{FBDH}$	Falling edge of $V_{FB}$ from $0.25V$ to $0V$ to $V_{SW}$ rising edge		100		ns
FB propagation delay to output high	$T_{FBDL}$	Rising edge of $V_{FB}$ from $0V$ to $0.25V$ to $V_{SW}$ falling edge		100		ns
Thermal shutdown <sup>(6)</sup>		Hysteresis = $20^{\circ}C$		150		$^{\circ}C$

### NOTES:

5) Guaranteed by design, not tested.

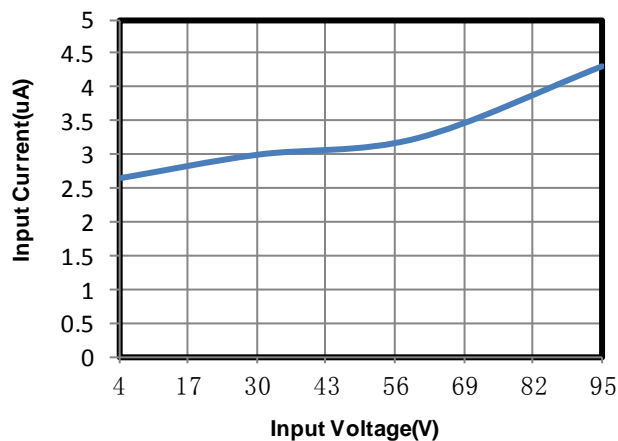
6) Guaranteed by characterization, not production tested.

# TYPICAL ELECTRICAL CHARACTERISTICS

$V_{IN} = 60V$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted.

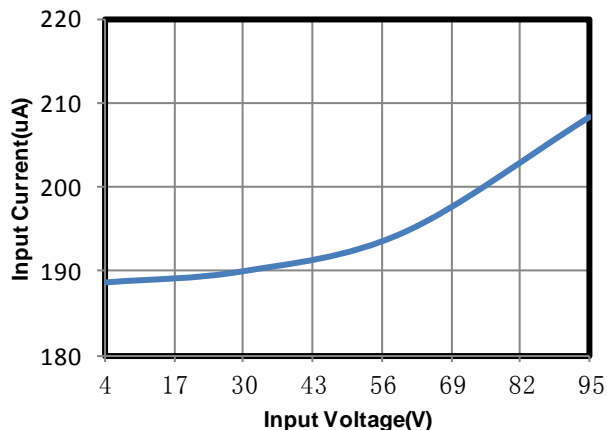
Shutdown Current vs. Input Voltage

EN=LOW



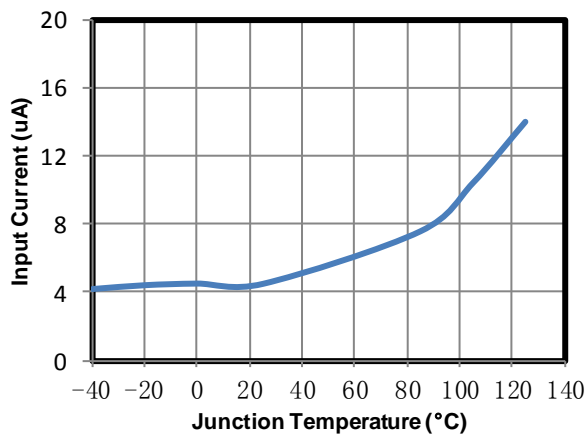
Quiescent Current vs. Input Voltage

EN=HIGH, DIM=LOW,  $V_{FB}=250mV$



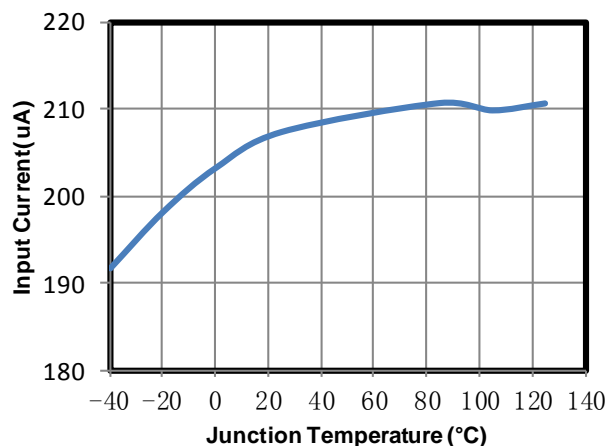
Shutdown Current vs. Temperature

$V_{IN}=95V$ , EN=LOW

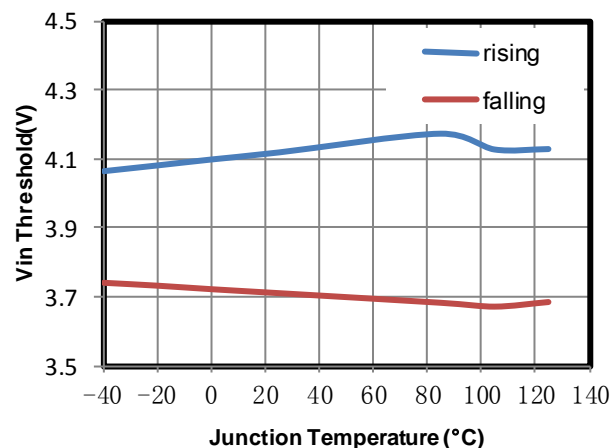


Quiescent Current vs. Temperature

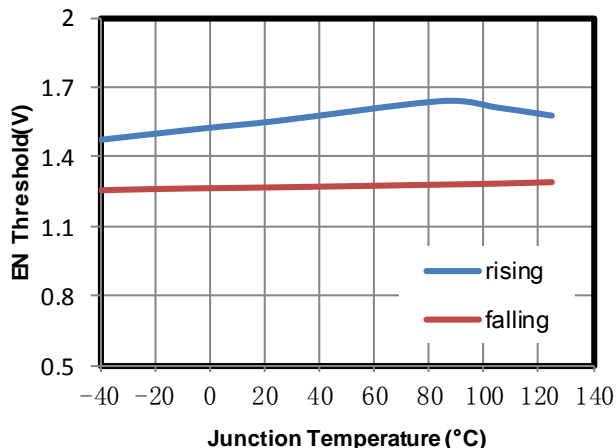
$V_{IN}=95V$ , DIM=LOW, EN=HIGH,  $V_{FB}=250mV$



UVLO Threshold vs. Temperature



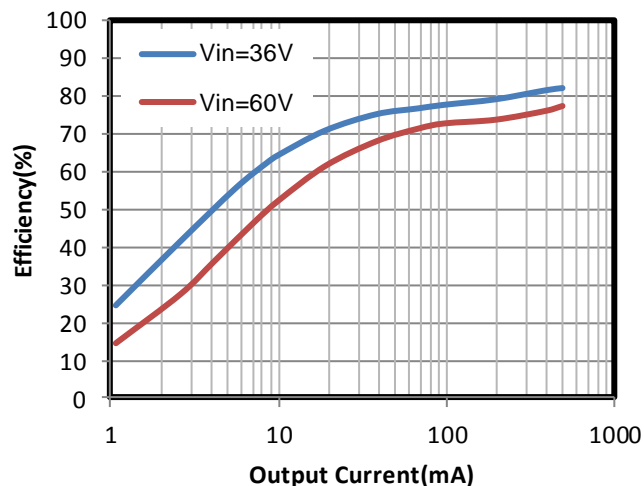
EN Threshold vs. Temperature



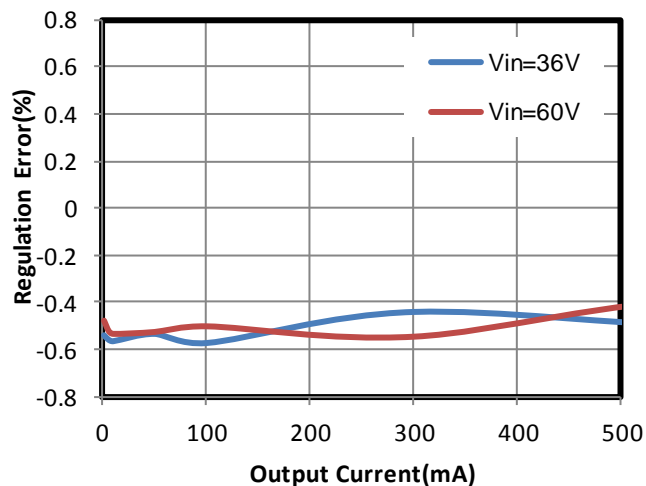
# TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

$V_{IN} = 60V$ ,  $V_{OUT} = 5V$ ,  $I_{OUT} = 1A$ ,  $L=33\mu H$ ,  $C_{OUT} = 100\mu F$ ,  $T_A = +25^{\circ}C$ , unless otherwise noted.

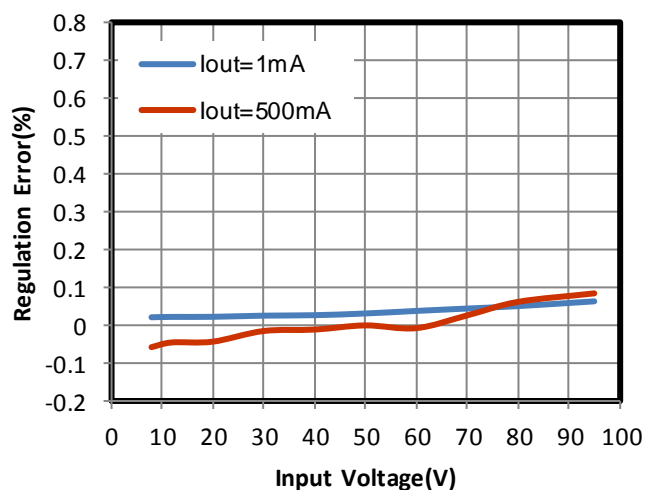
## Efficiency vs. Output Current



## Load Regulation



## Line Regulation

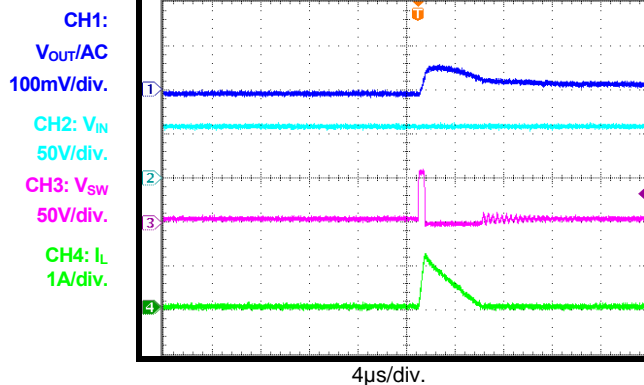


# TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

$V_{IN} = 60V$ ,  $V_{OUT} = 5V$ ,  $I_{OUT} = 1A$ ,  $L=33\mu H$ ,  $C_{OUT} = 100\mu F$ ,  $T_A = +25^\circ C$ , unless otherwise noted.

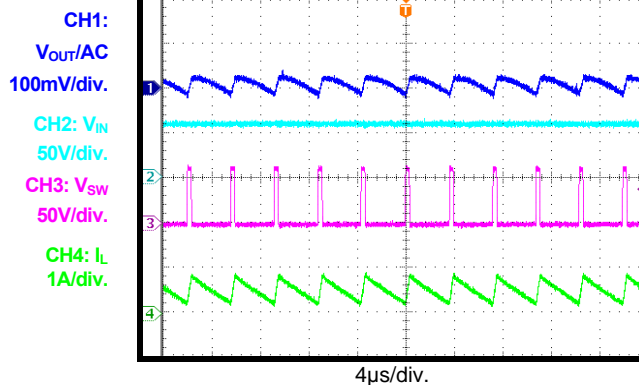
Steady State

$I_{OUT}=0A$



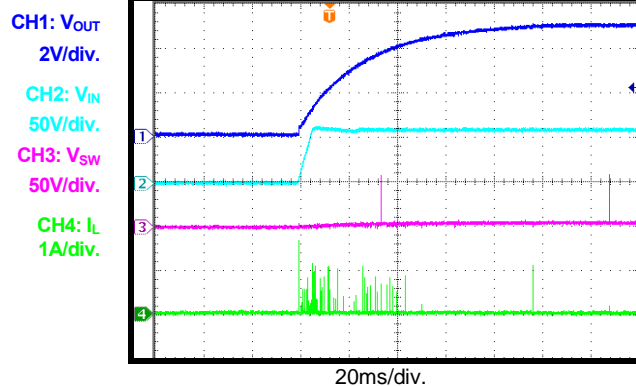
Steady State

$I_{OUT}=0.5A$



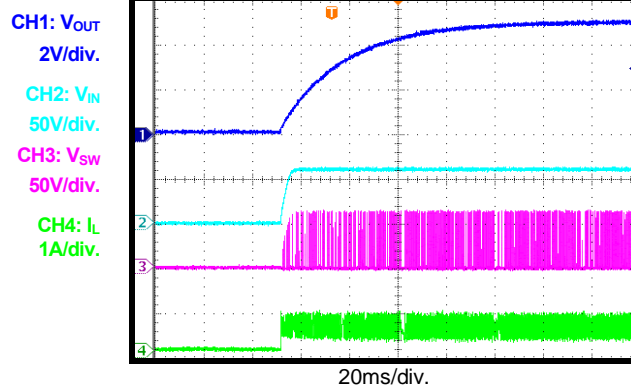
Power On

$I_{OUT}=0A$



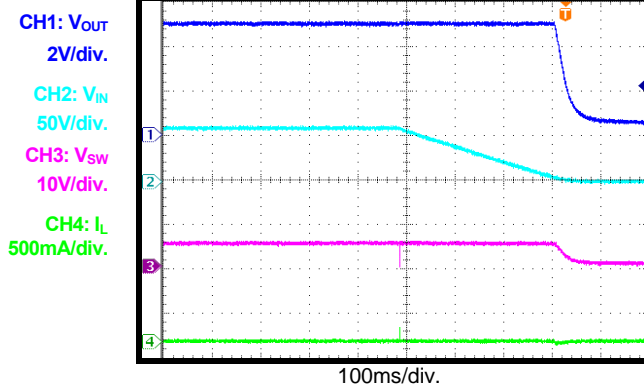
Power On

$I_{OUT}=0.5A$



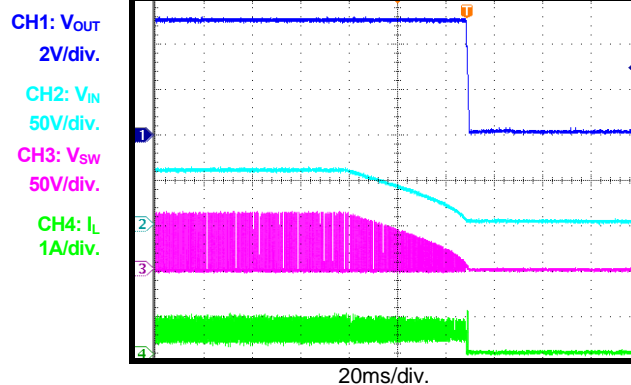
Power Off

$I_{OUT}=0A$



Power Off

$I_{OUT}=0.5A$

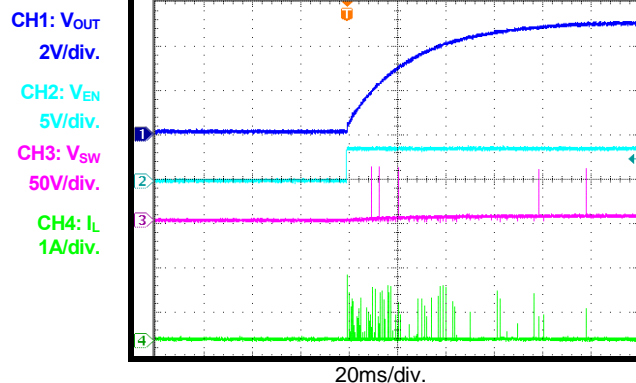


## TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

$V_{IN} = 60V$ ,  $V_{OUT} = 5V$ ,  $I_{OUT} = 1A$ ,  $L = 33\mu H$ ,  $C_{OUT} = 100\mu F$ ,  $T_A = +25^\circ C$ , unless otherwise noted.

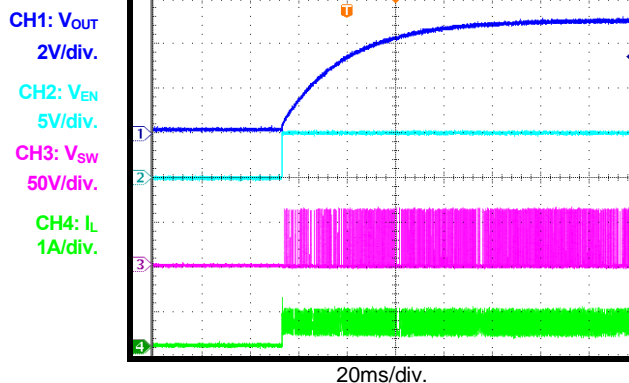
**EN Start-Up**

$I_{OUT} = 0A$



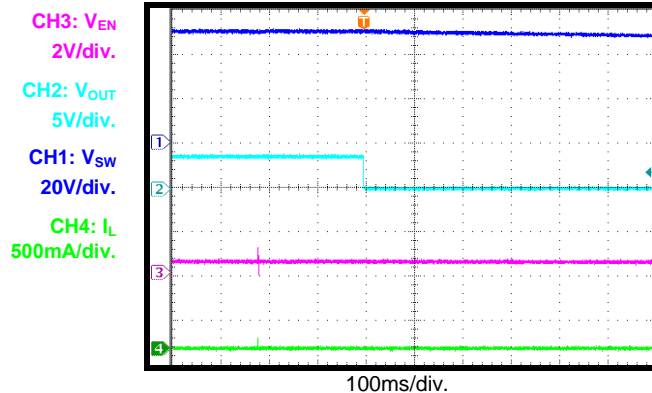
**EN Start-Up**

$I_{OUT} = 0.5A$



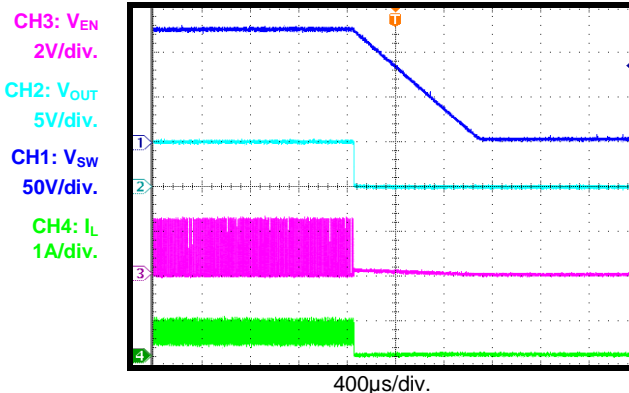
**EN Shutdown**

$I_{OUT} = 0A$



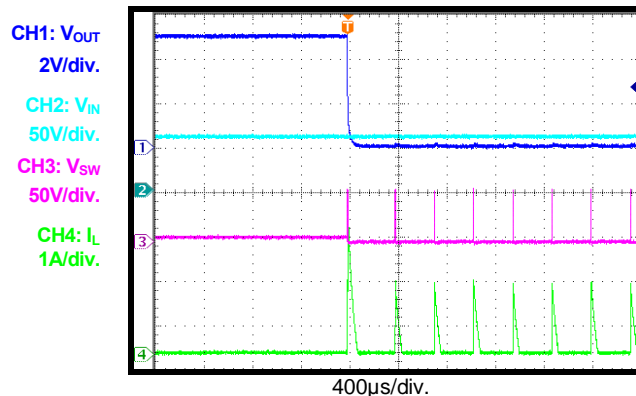
**EN Shutdown**

$I_{OUT} = 0.5A$



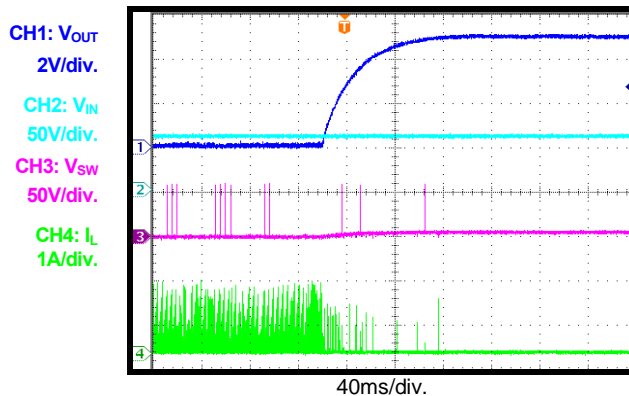
**SCP Entry**

$I_{OUT} = 0A$



**SCP Recovery**

$I_{OUT} = 0A$



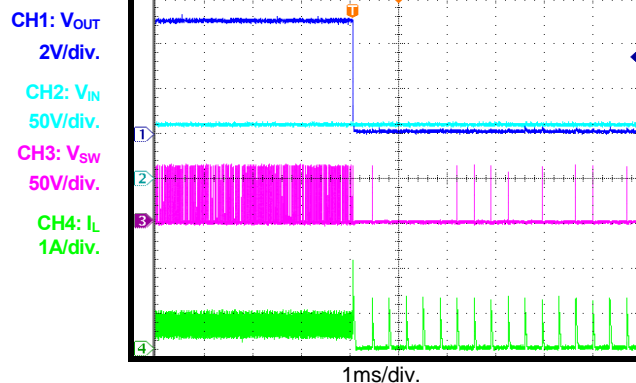


## TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

$V_{IN} = 60V$ ,  $V_{OUT} = 5V$ ,  $I_{OUT} = 1A$ ,  $L=33\mu H$ ,  $C_{OUT} = 100\mu F$ ,  $T_A = +25^\circ C$ , unless otherwise noted.

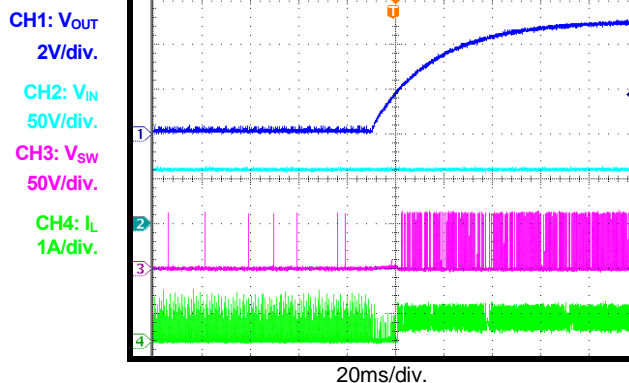
### SCP Entry

$I_{OUT}=0.5A$



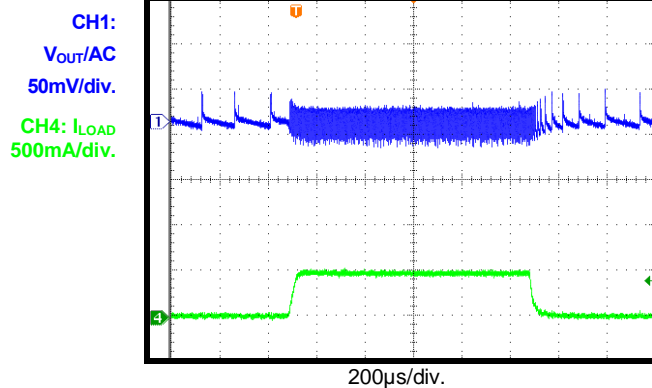
### SCP Recovery

$I_{OUT}=0.5A$ , E-load turn-on Threshold=0.32V



### Load Transient

$I_{OUT}=0A \rightarrow 0.5A$



## PIN FUNCTIONS

SOIC-8 EP Pin #	Name	Description
1	FB	<b>Feedback.</b> FB is the input to the voltage feedback hysteretic comparator.
2	NC	<b>No connection.</b> NC is not connected.
3	VIN	<b>Input supply.</b> VIN supplies power to all of the internal control circuitries, both BST regulators, and the high-side switch. A decoupling capacitor to ground must be placed close to VIN to minimize switching spikes.
4	BST	<b>Bootstrap.</b> BST is the positive power supply for the internal, floating, high-side MOSFET driver. Connect a bypass capacitor between BST and SW.
5	SW	<b>Switch node.</b> SW is the output from the high-side switch. A low forward voltage ( $V_F$ ) Schottky rectifier to ground is required. The rectifier must be placed close to SW to reduce switching spikes.
6	DIM	<b>PWM dimming input.</b> DIM is useful in LED driver applications. Pull DIM below the specified threshold for dimming off; pull DIM above the specified threshold for dimming on. If there is no need for a dimming function, such as in common buck applications, then connect DIM and EN together.
7	EN	<b>Enable input.</b> Pull EN below the specified threshold to shut down the MP9485; pull EN above the specified threshold or leave EN floating to enable the MP9485.
8	GND	<b>Ground.</b> GND should be placed as close to the output capacitor as possible to avoid the high-current switch paths. Connect the exposed pad to the GND plane for optimal thermal performance.

## BLOCK DIAGRAM

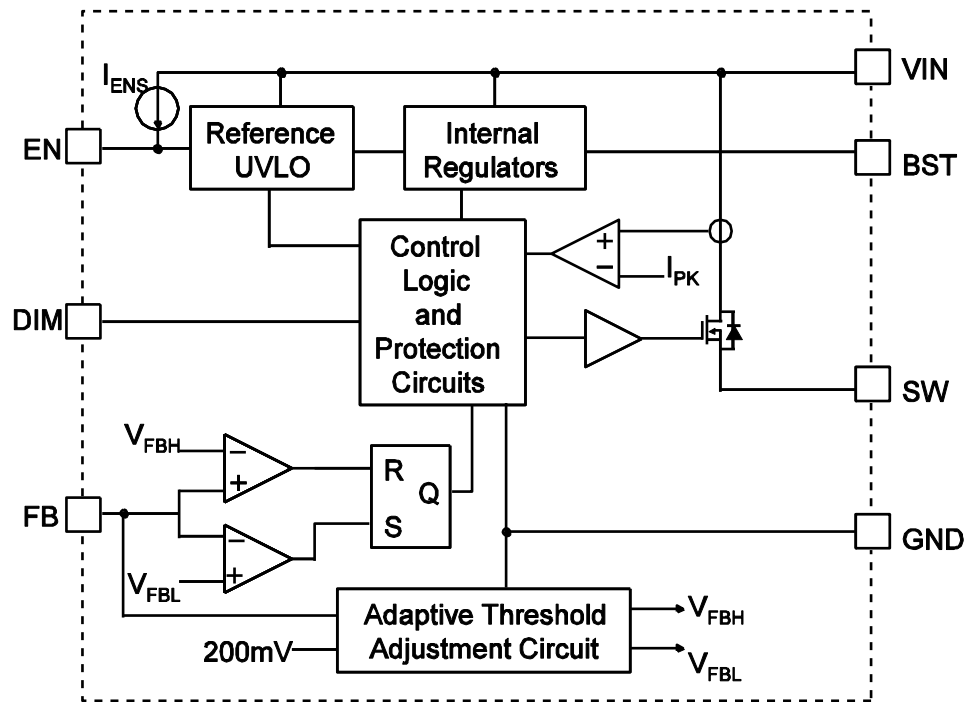


Figure 1: Functional Block Diagram

## OPERATION

### **Hysteresis Current Control with Adaptive Threshold Adjustment**

The MP9485 operates in a hysteretic voltage-mode control to regulate the output voltage. FB is connected to the tap of a resistor divider, which determines the output voltage. The power MOSFET is turned on and remains on until FB rises to 215mV. The power MOSFET is turned off and remains off until FB falls to 185mV. The two thresholds of 215mV and 185mV are adaptively adjusted to compensate for all the circuit delays so that the output voltage is regulated with an average 200mV value at FB.

### **Enable (EN) Control**

The MP9485 has a dedicated enable control pin (EN) with positive logic. Its falling threshold is 1.23V, and its rising threshold is 1.55V (320mV higher).

When floating, EN is pulled up to about 3.0V by an internal 2 $\mu$ A current source, so it is enabled. A current capability over 2 $\mu$ A is needed to pull EN down.

### **Floating Driver and Bootstrap Charging**

The floating power MOSFET driver is powered by an external bootstrap capacitor. This floating driver has its own UVLO protection. This UVLO's rising threshold is 2.2V with a threshold of 150mV.

The bootstrap capacitor is charged and regulated at about 5V by the dedicated internal bootstrap regulator.

If the internal circuit does not have sufficient voltage, and the bootstrap capacitor is not sufficiently charged, extra external circuitry can be used to ensure that the bootstrap voltage is in the normal operating region. Refer to the External Bootstrap Diode section on page 12 for more detail.

### **Under-Voltage Lockout (UVLO)**

Under-voltage lockout (UVLO) is implemented to protect the chip from operating at an insufficient supply voltage. The UVLO rising threshold is about 4.0V, while its falling threshold is a consistent 3.6V.

### **Dimming Function for LED Applications**

Because the FB reference of the MP9485 is very low, it is a good idea for the LED driver to have the LED current sense resistor connected between FB and GND. In such applications, the MP9485 uses DIM for dimming. To achieve dimming, apply a pulse on DIM. The high level of the pulse should be >1.5V, and the low level should be <0.5V. The frequency can be as high as 20kHz.

### **Thermal Shutdown**

Thermal shutdown is implemented to prevent the chip from operating at exceedingly high temperatures. When the silicon die temperature is higher than its upper threshold, the entire chip shuts down. When the temperature is lower than its lower threshold, the chip is enabled again.

### **Output Short Protection**

The output voltage is well-regulated when the FB voltage is around 200mV. If the output is pulled low in over-current protection (OCP) or is shorted to GND directly, the FB voltage is low, even though the power MOSFET is turned on. The power MOSFET is shut off if the failure time is longer than 10 $\mu$ s. The MP9485 attempts the operation again after a delay of about 300 $\mu$ s.

The power MOSFET current is also accurately sensed via a current sense MOSFET. If the current is over the current limit, the IC is shut down. This offers extra protection under output-short conditions.

## APPLICATION INFORMATION

### Setting the Output Voltage

The output voltage ( $V_{OUT}$ ) is set by a divider resistor ( $R1$  and  $R2$ ) (see the Typical Application on page 1). To achieve good noise immunity and low power loss,  $R2$  is recommended to be in the range of  $5k\Omega$  to  $50k\Omega$ .  $R1$  can then be determined with Equation (1):

$$R1 = \frac{V_{OUT} - V_{FB}}{V_{FB}} \times R2 \quad (1)$$

Where  $V_{FB} = 0.2V$ , typically.

### Output Capacitor and Frequency Setting

The output capacitor ( $C_{OUT}$ ) is necessary to achieve a smooth output voltage. The ESR of the capacitor should be sufficiently large compared to the capacitance; otherwise, the system may behave in an unexpected way, and the current ripple may be very high.  $V_{FB}$  changes from  $185mV$  to  $215mV$  when the power MOSFET switches from on to off. To charge the capacitor and generate  $215mV$  at FB, the system needs ESR and some inductor current. For example, for a  $5V$   $V_{OUT}$ , if the forward capacitor is  $0.1\mu F$ , the suggested ESR range of the output capacitor is  $100m\Omega$  to  $250m\Omega$ . Tantalum or aluminum electrolytic capacitors with a small ceramic capacitor are recommended.

A forward capacitor across  $R1$  is recommended when the output capacitor is tantalum or aluminum electrolytic, which can set the wanted frequency if the output capacitor and ESR cannot be changed. The forward capacitor can reduce the output voltage ripple.

### Selecting the Inductor

An inductor ( $L_O$ ) is required to convert the switching voltage to a smooth current to the load. Although the output current is low, it is recommended that the inductor current be continuous in each switching period to prevent reaching the current limit. Calculate the inductor value with Equation (2):

$$L = \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{F_{SW} \times I_{OUT} \times V_{IN} \times K} \quad (2)$$

Where  $K$  is a coefficient of about  $0.15 \sim 0.85$ .

### Output Rectifier Diode

The output rectifier diode supplies current to the inductor when the high-side switch is off. To reduce losses due to the diode forward voltage and recovery times, use a Schottky diode.

Choose a diode with a maximum reverse voltage rating greater than the maximum input voltage and a current rating greater than the average diode current.

### Input Capacitor ( $C_{IN}$ )

The input current to the step-down converter is discontinuous and therefore requires a capacitor to supply AC current to the step-down converter while maintaining the DC input voltage. Use low ESR capacitors for the best performance, especially under high switching frequency applications.

The RMS current through the input capacitor can be calculated with Equation (3):

$$I_{C1} = I_{OUT} \times \sqrt{\frac{V_{OUT}}{V_{IN}} \times (1 - \frac{V_{OUT}}{V_{IN}})} \quad (3)$$

With low ESR capacitors, the input voltage ripple can be estimated with Equation (4):

$$\Delta V_{IN} = \frac{I_{OUT} \times V_{OUT}}{F_{SW} \times C_{IN} \times V_{IN}} \times (1 - \frac{V_{OUT}}{V_{IN}}) \quad (4)$$

Choose an input capacitor with enough RMS current rating and enough capacitance for small input voltage ripples.

When electrolytic or tantalum capacitors are applied, a small, high-quality ceramic capacitor (i.e.:  $0.1\mu F$ ) should be placed as close to the IC as possible.

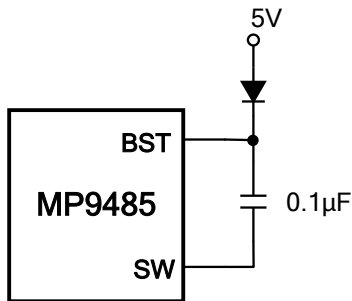
### External Bootstrap Diode

An external bootstrap diode may enhance the efficiency of the converter (see Figure 2). An external BST diode is recommended from the  $5V$  supply to BST in the following cases:

- There is a  $5V$  rail available in the system
- $V_{IN}$  is no greater than  $5V$
- $V_{OUT}$  is between  $3.3V$  and  $5V$

This diode is also recommended for high duty cycle operation (when  $V_{OUT}/V_{IN} > 65\%$ ) and very high frequency (over  $1.5MHz$ ) applications.

The bootstrap diode can be a low-cost one, such as IN4148 or BAT54.

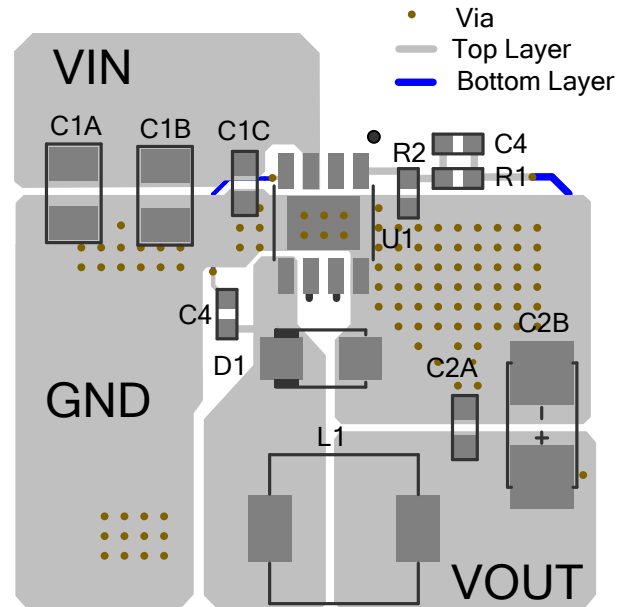


**Figure 2: External Bootstrap Diode**

### PCB Layout Guidelines

Efficient PCB layout is critical for stable operation. Refer to Figure 3 and follow the guidelines below.

- 1, Place the input decoupling capacitor, catch diode, and MP9485 (VIN, SW, and PGND pin) as close to each other as possible.
- 2, Power traces should be short and wide to reduce voltage spikes on the SW node and lower EMI noise level.
- 3, Run the feedback trace as far from the inductor and noisy power traces as possible.
- 4, Thermal vias with 15mil barrel diameter and 40mil pitch (instance between the centers) are suggested under the exposed pad to improve thermal conduction.



**Figure 3: Layout Recommendation**

### Design Example

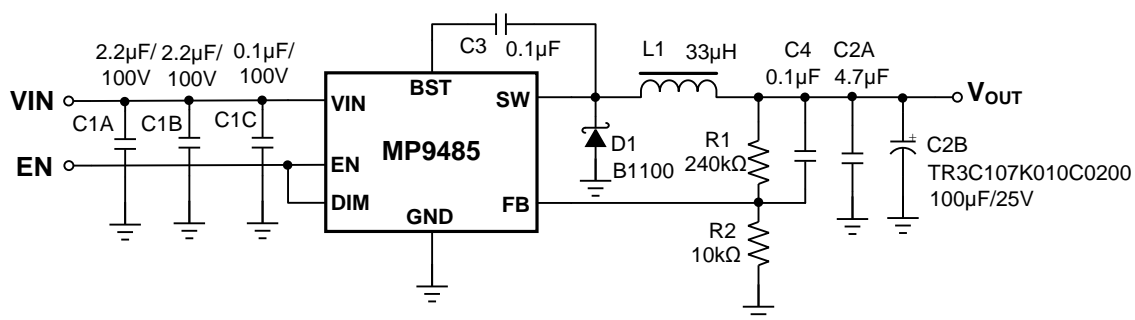
Table 1 is a design example following the application guidelines for the specifications below.

**Table 1: Design Example**

<b>V<sub>IN</sub></b>	8V to 95V
<b>V<sub>OUT</sub></b>	5V
<b>I<sub>OUT</sub></b>	0A to 0.5A

The typical application circuit for  $V_{OUT} = 5V$  in Figure 4 shows the detailed application schematic and is the basis for the typical performance waveforms. This circuit can work down to 4.5V after start-up, but  $V_{OUT}$  may drop when  $V_{IN}$  is low due to the maximum duty cycle limit. For more detailed device applications, please refer to the related evaluation board datasheet.

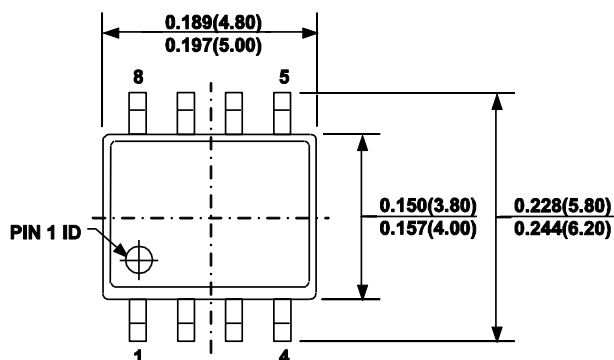
## TYPICAL APPLICATION CIRCUIT



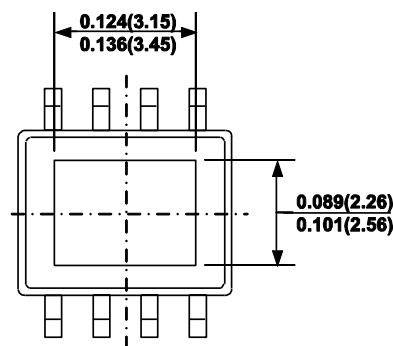
**Figure 4:  $V_{IN} = 60V$ ,  $V_{OUT} = 5V$ ,  $I_{OUT} = 0.5A$**

# PACKAGE INFORMATION

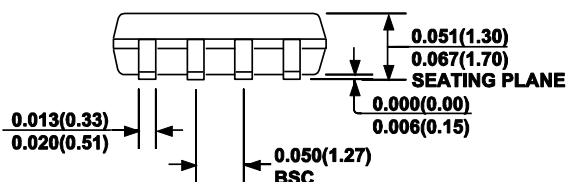
## SOIC-8 EP



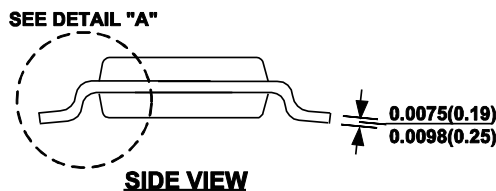
TOP VIEW



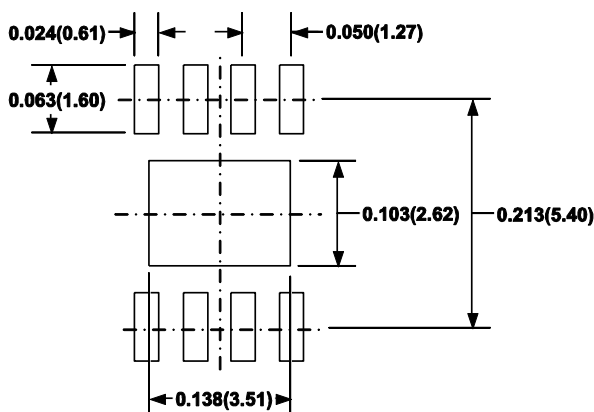
BOTTOM VIEW



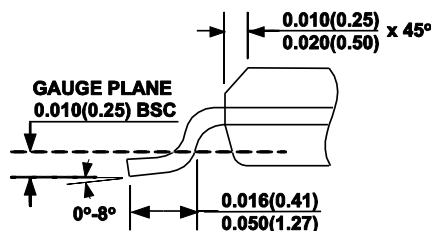
FRONT VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN



DETAIL "A"

### NOTE:

- 1) CONTROL DIMENSION IS IN INCHES. DIMENSION IN BRACKET IS IN MILLIMETERS.
- 2) PACKAGE LENGTH DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- 3) PACKAGE WIDTH DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- 4) LEAD COPLANARITY (BOTTOM OF LEADS AFTER FORMING) SHALL BE 0.004" INCHES MAX.
- 5) DRAWING CONFORMS TO JEDEC MS-012, VARIATION BA.
- 6) DRAWING IS NOT TO SCALE.

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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